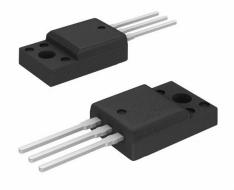


FDPF12N50FT Datasheet

www.digi-electronics.com



DiGi Electronics Part Number

FDPF12N50FT-DG

FDPF12N50FT

onsemi

Manufacturer Product Number

Description

Manufacturer

Detailed Description

MOSFET N-CH 500V 11.5A TO220F

N-Channel 500 V 11.5A (Tc) 42W (Tc) Through Hole TO-220F-3

https://www.DiGi-Electronics.com



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FDPF12N50FT	onsemi
Series:	Product Status:
UniFET™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (ld) @ 25°C:
500 V	11.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	700mOhm @ 6A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
5V @ 250μΑ	30 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	1395 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	42W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-220F-3	TO-220-3 Full Pack
Base Product Number:	
FDPF12	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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FDPF12N50FT N-Channel UniFETTM FRFET[®] MOSFET 500 V, 11.5 A, 700 m Ω

Features

- $R_{DS(on)}$ = 590 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 6 A
- Low Gate Charge (Typ. 21 nC)
- Low C_{rss} (Typ. 11 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

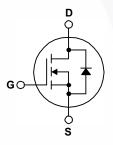
Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET[®] MOSFET has been enhanced by lifetime control. Its trr is less than 100nsec and the reverse dv/ dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDPF12N50FT	Unit
V _{DSS}	Drain to Source Voltage		500	V	
V _{GSS}	Gate to Source Voltage			±30	V
I _D Drain Curren	Drain Current	- Continuous (T _C = 25 ^o C)		11.5*	
	DrainCurrent	- Continuous (T _C = 100 ^o C)		6.9*	— A
I _{DM}	Drain Current	- Pulsed	(Note 1)	46*	А
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			456	mJ
I _{AR}	Avalanche Current (Note 1)		11.5	А	
E _{AR}	Repetitive Avalanche Energy (Note 1)		16.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	20	V/ns
P _D Power Dissipatio	Dewer Dissinction	(T _C = 25°C)		42	W
	Power Dissipation	- Derate Above 25°C		0.33	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

*Drain current limited by maximum junction temperature.

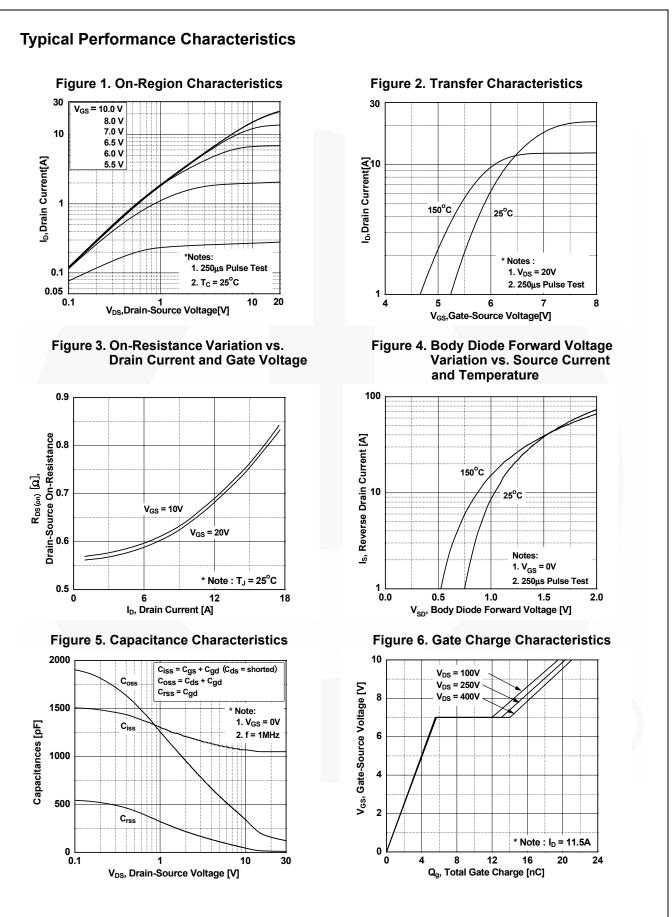
Thermal Characteristics

Symbol	Parameter	FDPF12N50FT	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.0	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/00	

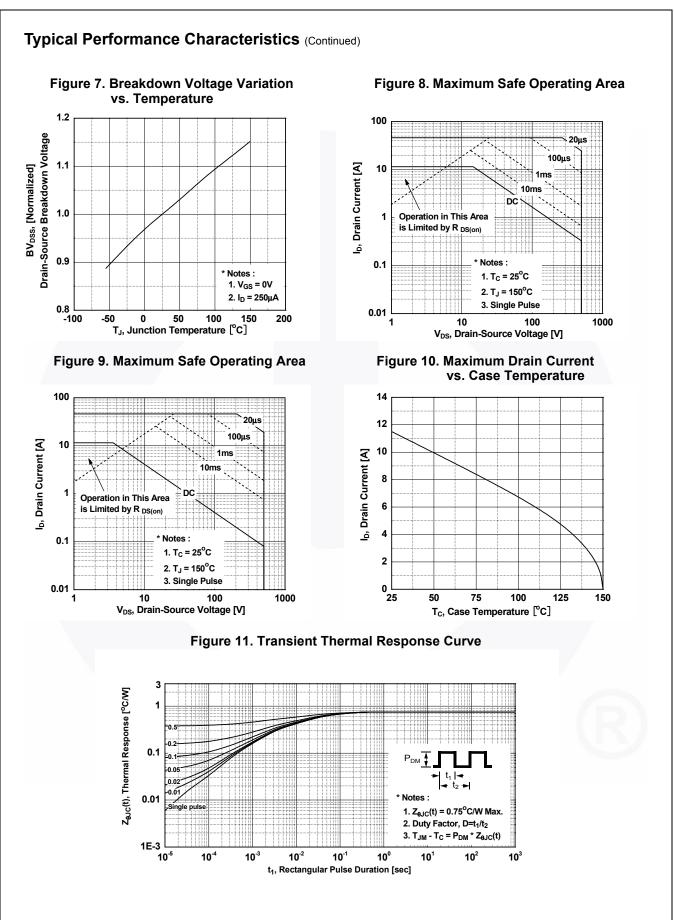
November 2013

Part Number Top Mark F		Package			e Ta	ape Width	Qu	antity	
FDPF12N50FT FDPF12N50FT TO-220					TO-220F		N/A	50 units	
Electrica	l Chara	acteristics T _C = 25°C	C unless othe	erwise noted.					
Symbol		Parameter		Test Condition	IS	Min.	Тур.	Max.	Unit
Off Charac	teristics	\$							
BV _{DSS}	Drain to	Source Breakdown Voltage	I _D =	= 250 μA, V _{GS} = 0 V, 1	L = 25 ^o C	500	-	-	V
ΔΒV _{DSS} / ΔΤ.Ι	Breakdo Coefficie	wn Voltage Temperature		250 μA, Referenced	-	-	0.5	-	V/°C
	Zero Ga	te Voltage Drain Current		$_{\rm S}$ = 500 V, V _{GS} = 0 V		-	-	10	μA
055	2010 00	to voltage Brain Ganone		_s = 400 V, T _C = 125 ^o C	;	-	-	100	μι
GSS	Gate to I	Body Leakage Current	V _G s	$_{\rm S}$ = ±30 V, V _{DS} = 0 V		-	-	±100	nA
On Charac	teristics	5							
V _{GS(th)}	Gate Th	reshold Voltage	V _G	_S = V _{DS} , I _D = 250 μA		3.0	-	5.0	V
R _{DS(on)}	Static Dr	ain to Source On Resistanc		_S = 10 V, I _D = 6 A		-	0.59	0.7	Ω
9 _{FS}	Forward	Transconductance	V _{DS}	_S = 40 V, I _D = 6 A		-	12	-	S
Dynamic C	haracte	ristics							
C _{iss}	1	pacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	1050	1395	pF
C _{oss}		Capacitance				_	135	180	pF
C _{rss}		Transfer Capacitance	t =			-	11	17	pF
Q _{g(tot)}		te Charge at 10V		V _{DS} = 400 V, I _D = 11.5 A, V _{GS} = 10 V (Note 4)		-	21	30	nC
Q _{gs}	-	Source Gate Charge				-	6	-	nC
Q _{gd}		Drain "Miller" Charge				-	9	-	nC
Switching							11		
-	_	Delay Time					21	50	ns
t _{d(on)}		Rise Time	Vor	V _{DD} = 250 V, I _D = 11.5 A,		-	45	100	ns
t <mark>r</mark>		Delay Time		$_{\rm S} = 10 \text{ V}, \text{ R}_{\rm G} = 25 \Omega$			50	110	ns
t _{d(off)} t _f		Fall Time		, c	(Note 4)		35	80	ns
	1				(11010 4)		55	00	113
		e Characteristics					·		i
						/ -	-	11.5	A
						-	-		A
						-	-	1.5	V
						-		· -	ns
	Reveise	Recovery Charge	urr/	αι – 100 Αγμ3		-	0.37	-	μC
. L = 6.9 mH, I _{AS} = . I _{SD} ≤ 11.5 A, di/d	Maximun Drain to 3 Reverse Reverse : pulse-width li = 11.5 A, V _{DD} tt ≤ 200 A/µs, 5	n Continuous Drain to Source Di n Pulsed Drain to Source Di Source Diode Forward Volta Recovery Time Recovery Charge imited by maximum junction tempera $= 50 \text{ V}, \text{ R}_{\text{G}} = 25 \Omega, \text{ starting } \text{ T}_{\text{J}} = 25^{\circ}\text{C}.$ erating temperature typical characteria	ode Forward age V _{GS} V _{GS} dI _F /			-		11.5 46 1.5 -	

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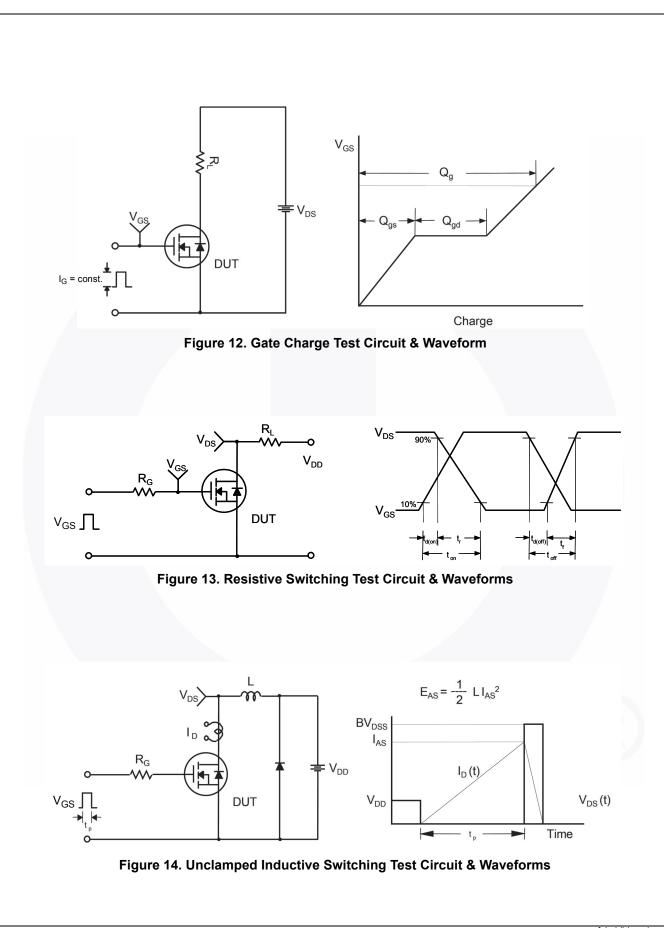


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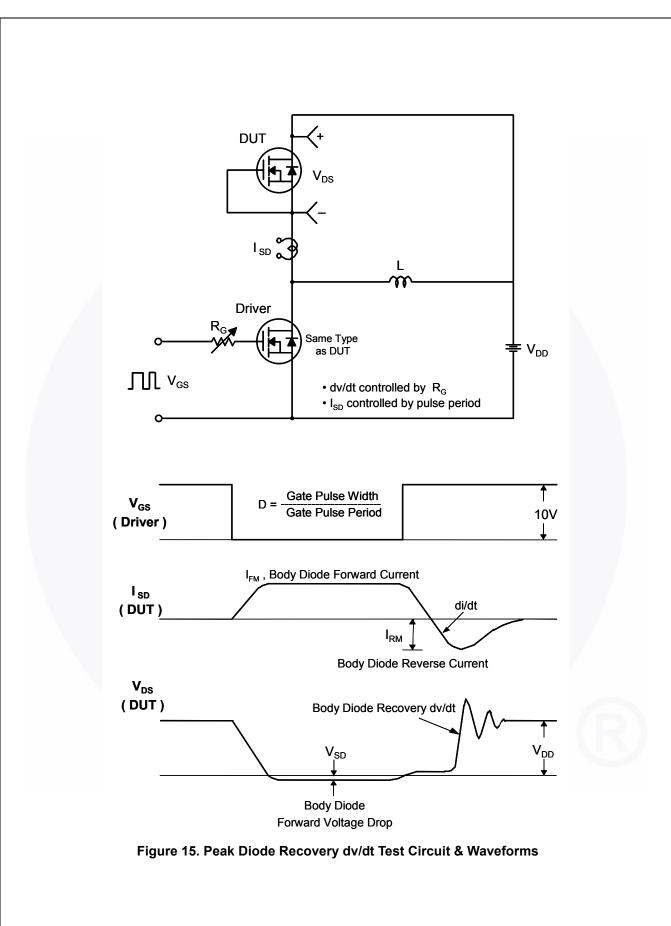
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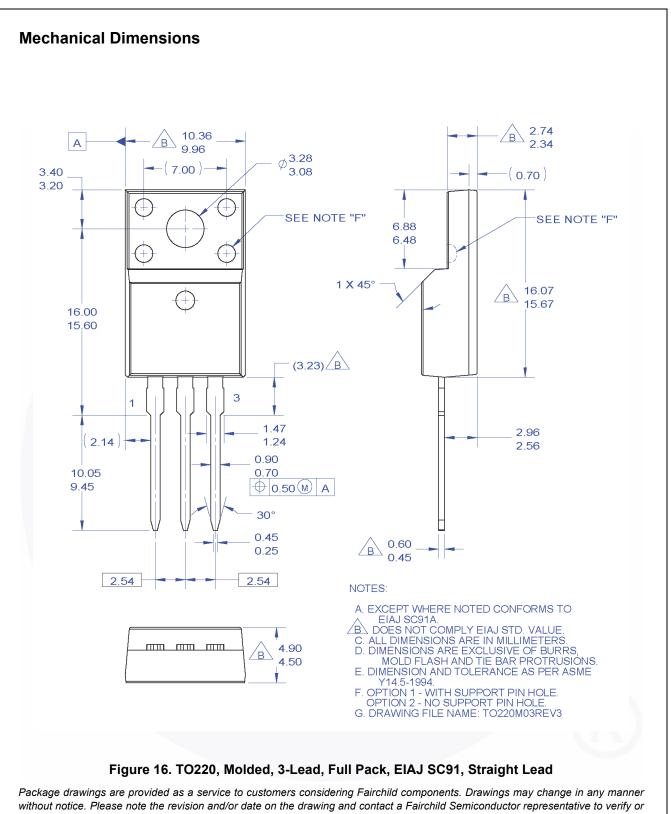
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